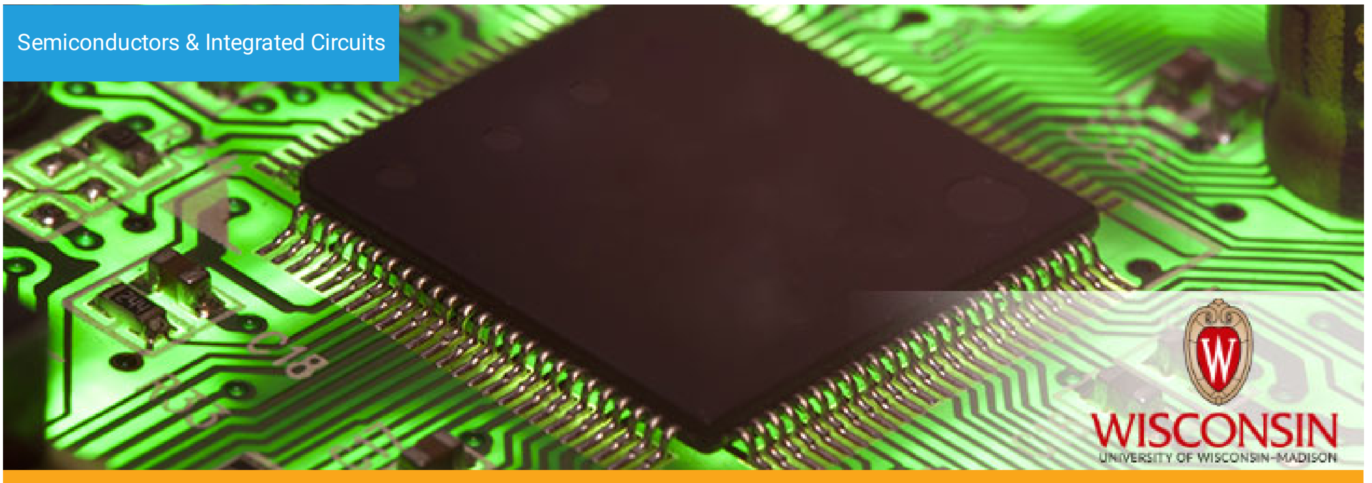

High-Quality, Single-Crystalline Silicon-Germanium Films

View U.S. Patent No. 10,176,991 in PDF format.

WARF: P170149US01

Inventors: Max Lagally, Thomas Kuech, Yingxin Guan, Shelley Scott, Abhishek Bhat, Xiaorui Cui

The Invention

High-quality, single-crystalline silicon-germanium (Si(1-x)Gex) having a high germanium content is provided. Layers of the high-quality, single-crystalline silicon-germanium can be grown to high sub-critical thicknesses and then released from their growth substrates to provide Si(1-x)Gex films without lattice mismatch-induced misfit dislocations or a mosaic distribution of crystallographic orientations.

Additional Information

For More Information About the Inventors

- Max Lagally
- Thomas Kuech

Tech Fields

- Semiconductors & Integrated Circuits : Components & materials

For current licensing status, please contact Jeanine Burmania at jeanine@warf.org or 608-960-9846

We use cookies on this site to enhance your experience and improve our marketing efforts. By continuing to browse without changing your browser settings to block or delete cookies, you agree to the storing of cookies and related technologies on your device. See our privacy policy

OK